

1 51. (Amended) A method of forming a transistor gate
2 comprising:
3 forming a gate oxide layer over a semiconductive substrate;
4 providing [at least one of] fluorine [or chlorine] within the gate
5 oxide layer; and
6 forming a gate proximate the gate oxide layer having the fluorine
7 therein after the providing.

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9
10 Please cancel claim 54.

11 *fully*
Subt C2
12 55. (Twice Amended) A method of forming a transistor gate
13 comprising:
14 forming a gate and a gate oxide layer in overlapping relation, the
15 gate having opposing edges and a center therebetween, the gate oxide
16 layer having a center and outwardly exposed opposing edges laterally
17 aligned with the edges of the gate; and
18 concentrating at least one of chlorine or fluorine in the gate oxide
19 layer having the outwardly exposed opposing edges and within the
20 overlap more proximate at least one of the outwardly exposed oxide
21 gate edges than the center.